



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

KTC3202 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

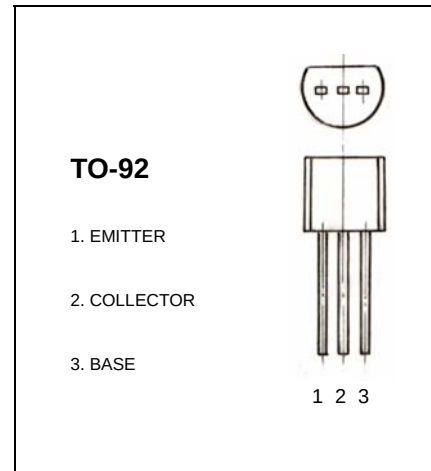
I_{CM} : 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 35 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-BASE breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1mA, I_B = 0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1mA, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 35V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1V, I_C = 100mA$	70		400	
	$h_{FE(2)}$	$V_{CE} = 6V, I_C = 400mA$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 10mA$		0.1	0.25	V
Base-Emitter Saturation Voltage	V_{BE}	$V_{CE} = 1V, I_C = 100mA$		0.8	1.0	V
Transition frequency	f_T	$V_{CE} = 6V, I_C = 20mA$		200		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 6V, I_E = 0, f = 1MHz$		7.0		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR
Range	70-140	120-240	200-400